

**AMENDMENTS TO THE SPECIFICATION**

Please replace paragraph [0032] of the specification with the following amended paragraph:

[0032] Gate dielectric **110** can be formed on a surface of substrate **100** utilizing any conventional deposition process including, for example, chemical vapor deposition (CVD), plasma-assisted CVD, plasma assisted oxidation, thermal deposition, atomic layer CVD, evaporation, sputtering, remote plasma nitridization (RPN), and chemical solution deposition. Gate dielectric **110** is not limited to any particular material may comprise any number of materials, or combinations of materials, suitable for use as a gate dielectric. For example, gate dielectric **110** may comprise any conventional dielectric material such as, ~~such as~~, for example, silicon oxides, silicon nitrides, silicon oxynitrides and mixtures, alloys, or multilayers thereof. It may also comprise a high-k material such as, for example, HfO<sub>2</sub>, ZrO<sub>2</sub>, HfSiO<sub>2</sub>, ZrSiO<sub>2</sub>, AlSi, and mixtures, alloys, or multilayers thereof. A preferred material for the gate dielectric is SiO<sub>2</sub>.